

**N-Channel Logic Level Enhancement Mode Power MOSFET**

# MTB06N03H8

BV <sub>DSS</sub>	30V
I <sub>D</sub>	75A
R <sub>DS(on)(max)</sub>	6.5mΩ

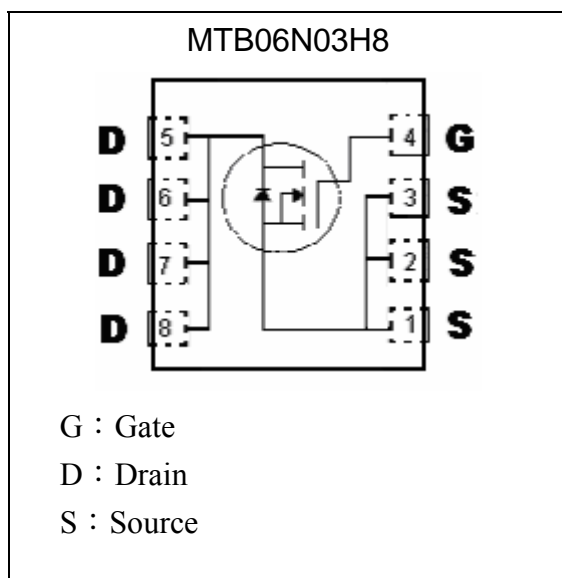
## Description

The MTB06N03H8 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.

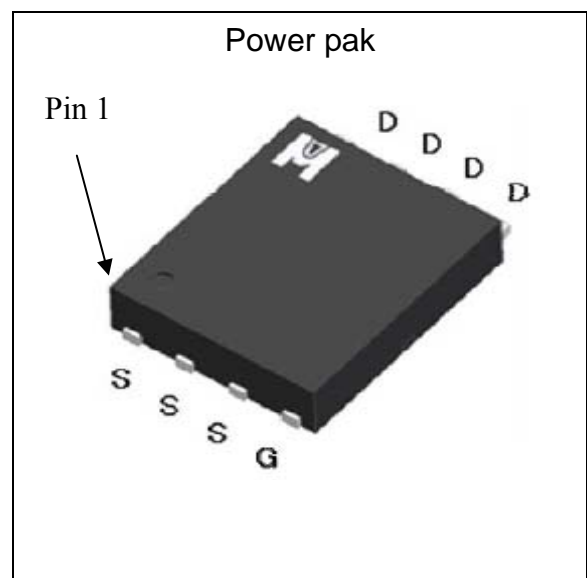
## Features

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Dynamic dv/dt rating
- Repetitive Avalanche Rated
- Pb-free lead plating and Halogen-free package

## Symbol



## Outline





**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage	V <sub>GS</sub>	±20		
Continuous Drain Current @ Tc=25°C	I <sub>D</sub>	75	A	
Continuous Drain Current @ Tc=100°C		45		
Pulsed Drain Current	I <sub>DM</sub>	160 *1		
Avalanche Current	I <sub>AS</sub>	53		
Avalanche Energy @ L=0.1mH, I <sub>D</sub> =53A, R <sub>G</sub> =25 Ω	E <sub>AS</sub>	140	mJ	
Repetitive Avalanche Energy @ L=0.05mH	E <sub>AR</sub>	40 *2		
Total Power Dissipation	P <sub>D</sub>	Tc=25°C	60	W
		Tc=100°C	32	
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55~+175	°C	

100% UIS testing in condition of V<sub>D</sub>=15V, L=0.1mH, V<sub>G</sub>=10V, I<sub>L</sub>=40A, Rated V<sub>DS</sub>=25V N-CH

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R <sub>th,j-c</sub>	2.5	°C/W
Thermal Resistance, Junction-to-ambient, max	R <sub>th,j-a</sub>	50 *3	°C/W

- Note : 1. Pulse width limited by maximum junction temperature  
 2. Duty cycle ≤ 1%  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, 125°C/W when mounted on minimum copper pad

**Characteristics (Tc=25°C, unless otherwise specified)**

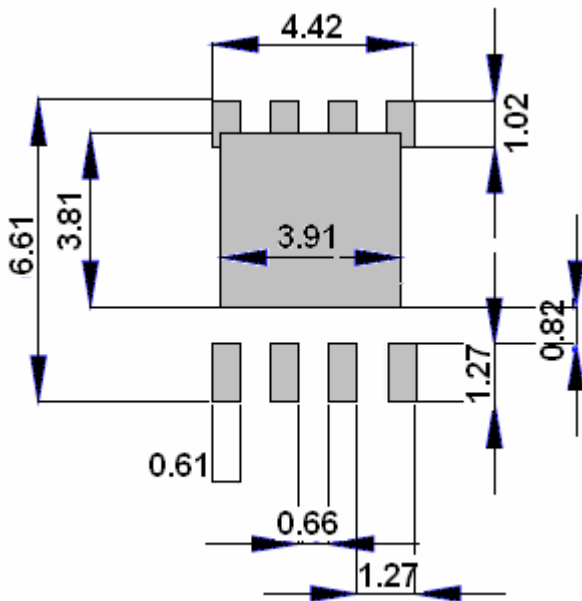
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	1.0	1.5	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA
G <sub>FS</sub> *1	-	25	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =24A
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =24V, V <sub>GS</sub> =0
	-	-	25		V <sub>DS</sub> =20V, V <sub>GS</sub> =0, T <sub>j</sub> =125°C
I <sub>D(ON)</sub> *1	75	-	-	A	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V
R <sub>DS(ON)</sub> *1	-	5.5	6.5	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =30A
	-	8.8	11	mΩ	V <sub>GS</sub> =4.5V, I <sub>D</sub> =24A
<b>Dynamic</b>					
C <sub>iss</sub>	-	3292	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz
C <sub>oss</sub>	-	501	-		
C <sub>rss</sub>	-	355	-		

**Characteristics (Tc=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Qg (VGS=10V) *1, 2	-	48	-	nC	VDS=15V, VGS=10V, ID=30A
Qg (VGS=4.5V) *1, 2	-	27	-		
Qgs *1, 2	-	6	-		
Qgd *1, 2	-	16	-		
td(ON) *1, 2	-	20	-	ns	VDS=15V, ID=24A, VGS=10V, RGS=2.7Ω
tr *1, 2	-	15	-		
td(OFF) *1, 2	-	65	-		
tf *1, 2	-	10	-		
Rg	-	1.2	-	Ω	VGS=15mV, VDS=0V, f=1MHz
<b>Source-Drain Diode</b>					
IS *1	-	-	75	A	
ISM *3	-	-	150		
VSD*1	-	-	1.3	V	IF=IS, VGS=0V
trr	-	32	-	ns	IF=IS, dIF/dt=100A/μs
Qrr	-	12	-	nC	

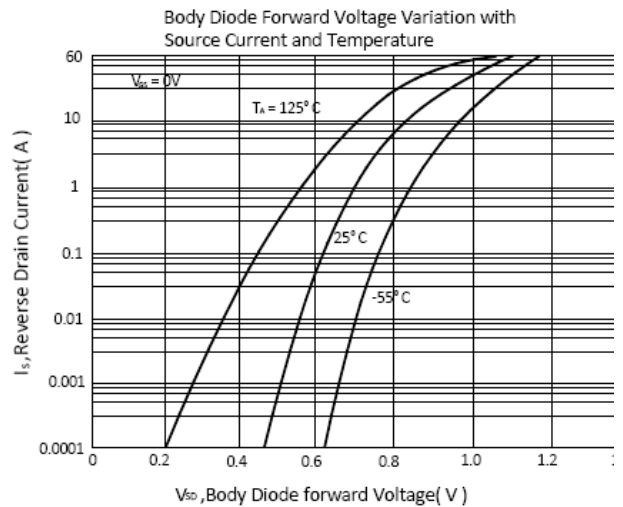
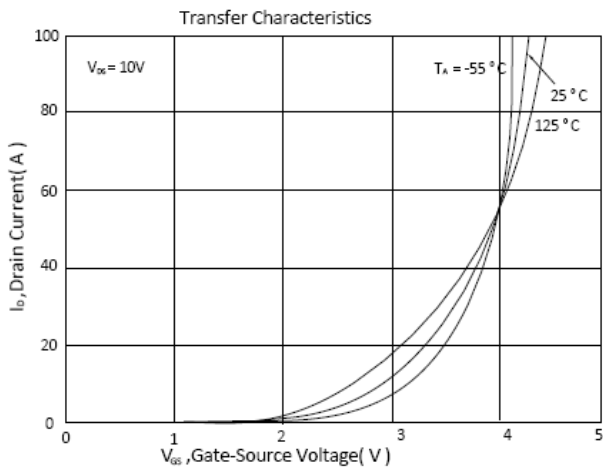
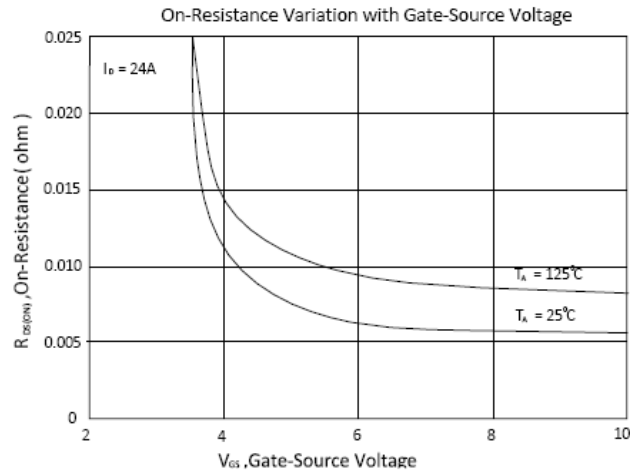
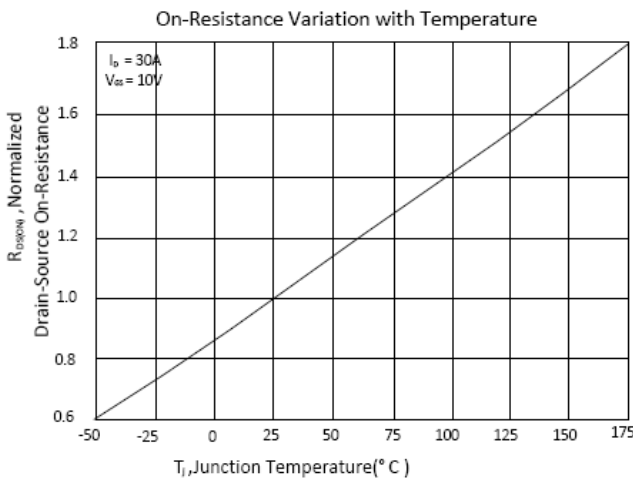
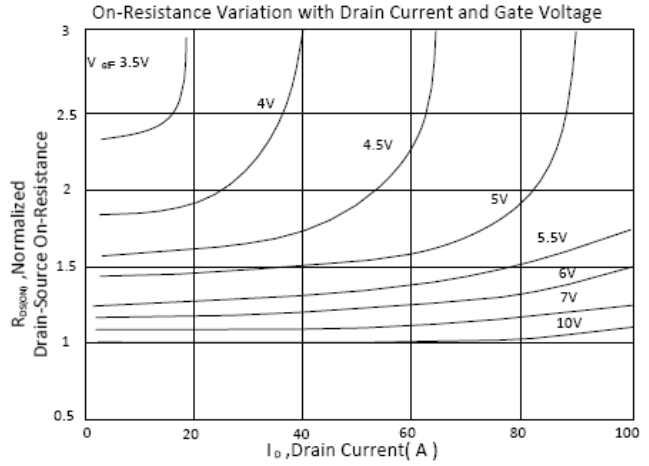
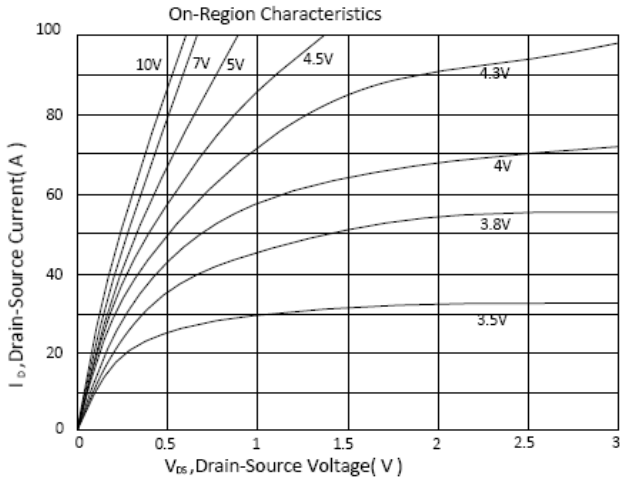
Note : \*1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%  
 \*2.Independent of operating temperature  
 \*3.Pulse width limited by maximum junction temperature.

**Recommended Footprint**



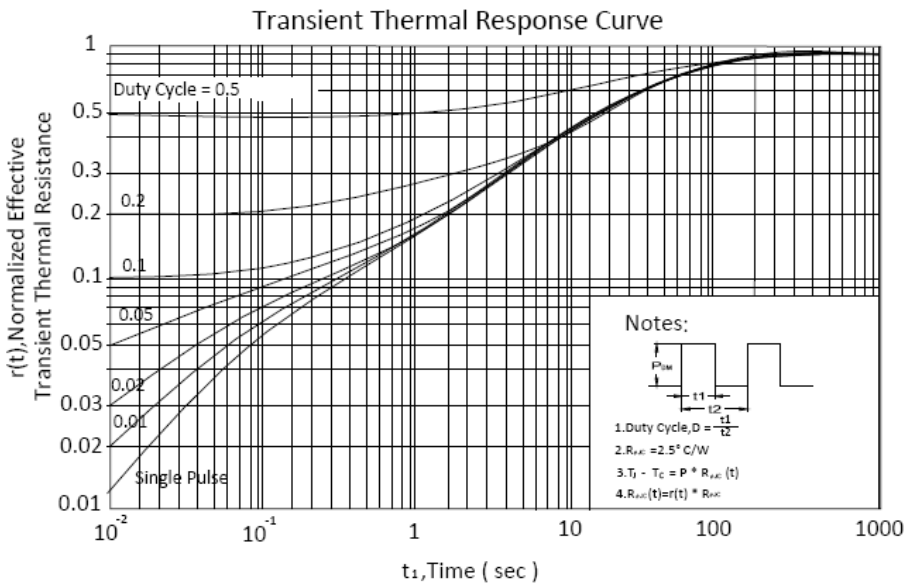
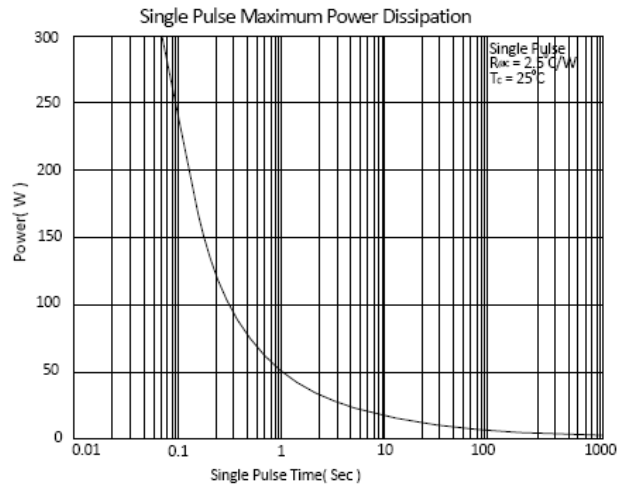
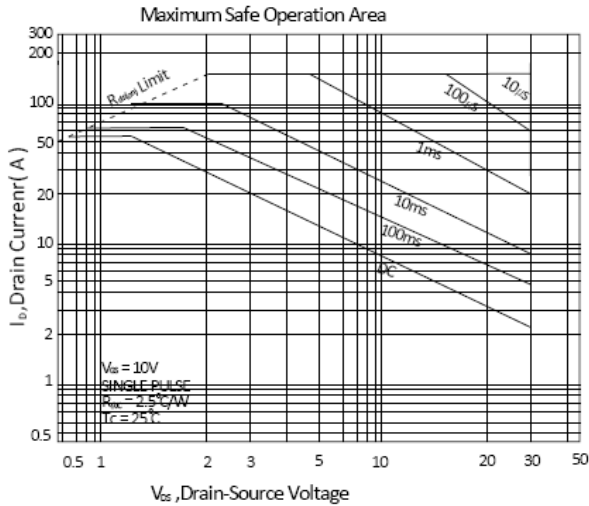
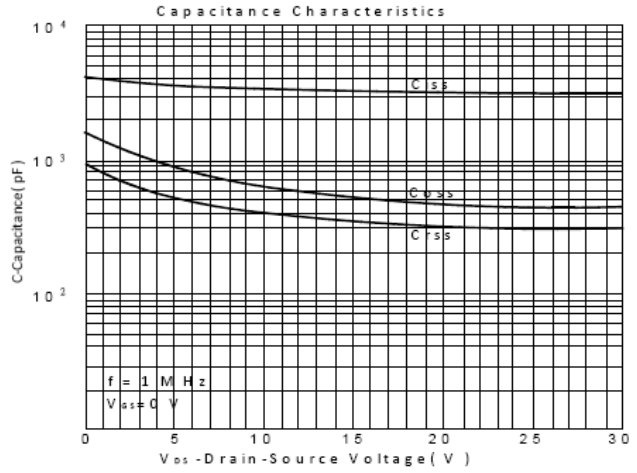
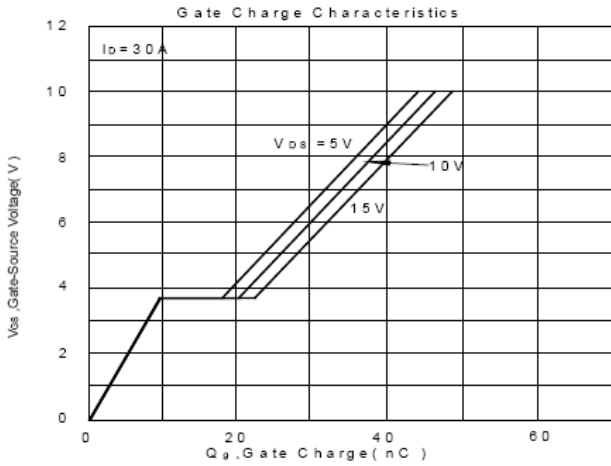
unit : mm

**Characteristic Curves**

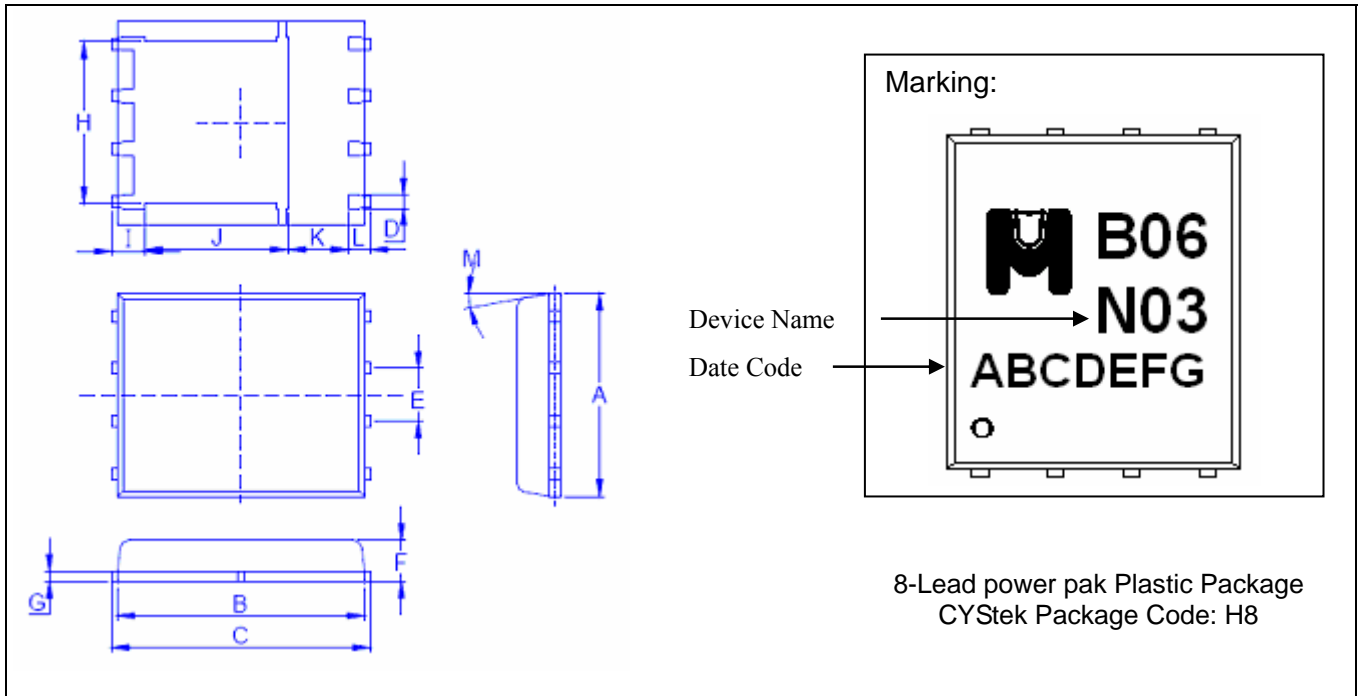




**Characteristic Curves(Cont.)**



**Power pak Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1890	0.1969	4.80	5.00	I	0.0161	0.0240	0.41	0.61
B	0.2244	0.2283	5.70	5.80	J	0.1331	0.1488	3.38	3.78
C	0.2323	0.2402	5.90	6.10	K	0.0433	-	1.10	-
D	0.0130	0.0201	0.33	0.51	L	0.0201	0.0280	0.51	0.71
E	0.0500*		1.27*		M	-	-	0°	12°
F	0.0354	0.0472	0.90	1.20					
G	0.0067	0.0118	0.17	0.30					
H	0.1445	0.1583	3.67	4.02					

- Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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